

Feng Wang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

65
papers

12,732
citations

38
h-index

66
g-index

66
ext. papers

14,582
ext. citations

14.5
avg, IF

6.12
L-index

#	Paper	IF	Citations
65	Growth, Raman Scattering Investigation and Photodetector Properties of 2D SnP.. <i>Small</i> , 2022 , e21080171	17.1	2
64	Recent progress on emergent two-dimensional magnets and heterostructures. <i>Nanotechnology</i> , 2021 , 32,	3.4	6
63	Reconfigurable photovoltaic effect for optoelectronic artificial synapse based on ferroelectric p-n junction. <i>Nano Research</i> , 2021 , 14, 4328	10	4
62	Controlled synthesis and Raman study of a 2D antiferromagnetic P-type semiconductor: FMnSe . <i>Nanoscale</i> , 2021 , 13, 6953-6964	7.7	4
61	Two-Dimensional Unipolar Memristors with Logic and Memory Functions. <i>Nano Letters</i> , 2020 , 20, 4144-4153	15.3	27
60	Gate-Coupling-Enabled Robust Hysteresis for Nonvolatile Memory and Programmable Rectifier in Van der Waals Ferroelectric Heterojunctions. <i>Advanced Materials</i> , 2020 , 32, e1908040	24	39
59	Subthermionic field-effect transistors with sub-5 μm gate lengths based on van der Waals ferroelectric heterostructures. <i>Science Bulletin</i> , 2020 , 65, 1444-1450	10.6	8
58	Robust trap effect in transition metal dichalcogenides for advanced multifunctional devices. <i>Nature Communications</i> , 2019 , 10, 4133	17.4	16
57	Anti-Ambipolar Transport with Large Electrical Modulation in 2D Heterostructured Devices. <i>Advanced Materials</i> , 2019 , 31, e1901144	24	10
56	Controlling Injection Barriers for Ambipolar 2D Semiconductors via Quasi-van der Waals Contacts. <i>Advanced Science</i> , 2019 , 6, 1801841	13.6	7
55	Van der Waals integration of 2D atomic crystals for advanced multifunctional devices. <i>Science Bulletin</i> , 2019 , 64, 1033-1035	10.6	4
54	Ultrathin Magnetic 2D Single-Crystal CrSe. <i>Advanced Materials</i> , 2019 , 31, e1900056	24	78
53	Strongly coupled van der Waals heterostructures for high-performance infrared phototransistor. <i>Applied Physics Letters</i> , 2019 , 114, 103501	3.4	14
52	Sub-millimeter-Scale Growth of One-Unit-Cell-Thick Ferrimagnetic CrS Nanosheets. <i>Nano Letters</i> , 2019 , 19, 2154-2161	11.5	67
51	Recent Progress in CVD Growth of 2D Transition Metal Dichalcogenides and Related Heterostructures. <i>Advanced Materials</i> , 2019 , 31, e1901694	24	131
50	Multibit Optoelectronic Memory in Top-Floating-Gated van der Waals Heterostructures. <i>Advanced Functional Materials</i> , 2019 , 29, 1902890	15.6	33
49	A unipolar nonvolatile resistive switching behavior in a layered transition metal oxide. <i>Nanoscale</i> , 2019 , 11, 20497-20506	7.7	12

48	Gapless van der Waals Heterostructures for Infrared Optoelectronic Devices. <i>ACS Nano</i> , 2019 , 13, 14519-14528	13	13
47	Van der Waals Heterostructure Devices with Dynamically Controlled Conduction Polarity and Multifunctionality. <i>Advanced Functional Materials</i> , 2019 , 29, 1804897	15.6	16
46	Uncovering the Conduction Behavior of van der Waals Ambipolar Semiconductors. <i>Advanced Materials</i> , 2019 , 31, e1805317	24	14
45	Nonvolatile infrared memory in MoS/PbS van der Waals heterostructures. <i>Science Advances</i> , 2018 , 4, eaap7916	14.3	106
44	WSe ₂ /GeSe heterojunction photodiode with giant gate tunability. <i>Nano Energy</i> , 2018 , 49, 103-108	17.1	49
43	2D library beyond graphene and transition metal dichalcogenides: a focus on photodetection. <i>Chemical Society Reviews</i> , 2018 , 47, 6296-6341	58.5	145
42	Impact of Thickness on Contact Issues for Pinning Effect in Black Phosphorus Field-Effect Transistors. <i>Advanced Functional Materials</i> , 2018 , 28, 1801398	15.6	32
41	Edge-Epitaxial Growth of 2D NbS ₂ -WS ₂ Lateral Metal-Semiconductor Heterostructures. <i>Advanced Materials</i> , 2018 , 30, e1803665	24	72
40	High-performance, multifunctional devices based on asymmetric van der Waals heterostructures. <i>Nature Electronics</i> , 2018 , 1, 356-361	28.4	123
39	Infrared-Sensitive Memory Based on Direct-Grown MoS ₂ -Upconversion-Nanoparticle Heterostructure. <i>Advanced Materials</i> , 2018 , 30, e1803563	24	57
38	Sub-10 nm Nanopattern Architecture for 2D Material Field-Effect Transistors. <i>Nano Letters</i> , 2017 , 17, 1065-1070	11.5	126
37	Configuration-dependent anti-ambipolar van der Waals p-n heterostructures based on pentacene single crystal and MoS ₂ . <i>Nanoscale</i> , 2017 , 9, 7519-7525	7.7	28
36	Multifunctional tunneling devices based on graphene/h-BN/MoSe ₂ van der Waals heterostructures. <i>Applied Physics Letters</i> , 2017 , 110, 173507	3.4	38
35	Van der Waals Epitaxial Growth of Atomic Layered HfS ₂ Crystals for Ultrasensitive Near-Infrared Phototransistors. <i>Advanced Materials</i> , 2017 , 29, 1700439	24	73
34	Progress on Electronic and Optoelectronic Devices of 2D Layered Semiconducting Materials. <i>Small</i> , 2017 , 13, 1604298	11	55
33	Ferroelectric-induced carrier modulation for ambipolar transition metal dichalcogenide transistors. <i>Applied Physics Letters</i> , 2017 , 110, 123106	3.4	17
32	Strain-Modulated Bandgap and Piezo-Resistive Effect in Black Phosphorus Field-Effect Transistors. <i>Nano Letters</i> , 2017 , 17, 6097-6103	11.5	88
31	Two-dimensional metal phosphorus trisulfide nanosheet with solar hydrogen-evolving activity. <i>Nano Energy</i> , 2017 , 40, 673-680	17.1	71

30	High-Performance Ultraviolet Photodetector Based on a Few-Layered 2D NiPS ₃ Nanosheet. <i>Advanced Functional Materials</i> , 2017 , 27, 1701342	15.6	170
29	Ultrathin Single-Crystalline CdTe Nanosheets Realized via Van der Waals Epitaxy. <i>Advanced Materials</i> , 2017 , 29, 1703122	24	90
28	Two-Dimensional Non-Layered Materials: Synthesis, Properties and Applications. <i>Advanced Functional Materials</i> , 2017 , 27, 1603254	15.6	124
27	Synthesis, properties and applications of 2D layered MX (M = Ga, In; X = S, Se, Te) materials. <i>Nanoscale</i> , 2016 , 8, 16802-16818	7.7	100
26	Epitaxial 2D PbS Nanoplates Arrays with Highly Efficient Infrared Response. <i>Advanced Materials</i> , 2016 , 28, 8051-8057	24	77
25	Toward High-Performance Top-Gate Ultrathin HfS ₂ Field-Effect Transistors by Interface Engineering. <i>Small</i> , 2016 , 12, 3106-11	11	42
24	Rational Design of Ultralarge Pb _{1-x} Sn _x Te Nanoplates for Exploring Crystalline Symmetry-Protected Topological Transport. <i>Advanced Materials</i> , 2016 , 28, 617-23	24	35
23	Oriented Growth of Pb _{1-x} Sn _x Te Nanowire Arrays for Integration of Flexible Infrared Detectors. <i>Advanced Materials</i> , 2016 , 28, 3596-601	24	31
22	Electrostatically tunable lateral MoTe ₂ p-n junction for use in high-performance optoelectronics. <i>Nanoscale</i> , 2016 , 8, 13245-50	7.7	34
21	Configuration-Dependent Electrically Tunable Van der Waals Heterostructures Based on MoTe ₂ /MoS ₂ . <i>Advanced Functional Materials</i> , 2016 , 26, 5499-5506	15.6	68
20	High-Performance Phototransistor of Epitaxial PbS Nanoplate-Graphene Heterostructure with Edge Contact. <i>Advanced Materials</i> , 2016 , 28, 6497-503	24	40
19	Ultrahigh sensitive MoTe ₂ phototransistors driven by carrier tunneling. <i>Applied Physics Letters</i> , 2016 , 108, 043503	3.4	78
18	Strong electrically tunable MoTe ₂ /graphene van der Waals heterostructures for high-performance electronic and optoelectronic devices. <i>Applied Physics Letters</i> , 2016 , 109, 193111	3.4	39
17	Ultrafast and ultrasensitive phototransistors based on few-layered HfSe ₂ . <i>Applied Physics Letters</i> , 2016 , 109, 213105	3.4	44
16	Integrated High-Performance Infrared Phototransistor Arrays Composed of Nonlayered PbS-MoS Heterostructures with Edge Contacts. <i>Nano Letters</i> , 2016 , 16, 6437-6444	11.5	79
15	van der Waals epitaxial ultrathin two-dimensional nonlayered semiconductor for highly efficient flexible optoelectronic devices. <i>Nano Letters</i> , 2015 , 15, 1183-9	11.5	116
14	Highly sensitive and fast phototransistor based on large size CVD-grown SnS ₂ nanosheets. <i>Nanoscale</i> , 2015 , 7, 14093-9	7.7	99
13	Synthesis, properties and applications of 2D non-graphene materials. <i>Nanotechnology</i> , 2015 , 26, 292001	3.4	82

12	Designing the shape evolution of SnSe ₂ nanosheets and their optoelectronic properties. <i>Nanoscale</i> , 2015 , 7, 17375-80	7.7	96
11	Tunable GaTe-MoS ₂ van der Waals p-n Junctions with Novel Optoelectronic Performance. <i>Nano Letters</i> , 2015 , 15, 7558-66	11.5	303
10	Sulfur vacancy activated field effect transistors based on ReS ₂ nanosheets. <i>Nanoscale</i> , 2015 , 7, 15757-62	7.7	36
9	Short channel field-effect transistors from ultrathin GaTe nanosheets. <i>Applied Physics Letters</i> , 2015 , 107, 153507	3.4	8
8	BN-Enabled Epitaxy of Pb(1-x)Sn(x)Se Nanoplates on SiO ₂ /Si for High-Performance Mid-Infrared Detection. <i>Small</i> , 2015 , 11, 5388-94	11	34
7	Enhanced Electrochemical H ₂ Evolution by Few-Layered Metallic WS ₂ (1-x)Se _{2x} Nanoribbons. <i>Advanced Functional Materials</i> , 2015 , 25, 6077-6083	15.6	98
6	Low-Dimensional Topological Crystalline Insulators. <i>Small</i> , 2015 , 11, 4613-24	11	19
5	Ultrasensitive Phototransistors Based on Few-Layered HfS ₂ . <i>Advanced Materials</i> , 2015 , 27, 7881-7	24	144
4	Ultrafast charge transfer in atomically thin MoS ₂ /WS ₂ heterostructures. <i>Nature Nanotechnology</i> , 2014 , 9, 682-6	28.7	1432
3	Giant bandgap renormalization and excitonic effects in a monolayer transition metal dichalcogenide semiconductor. <i>Nature Materials</i> , 2014 , 13, 1091-5	27	1150
2	Emerging photoluminescence in monolayer MoS ₂ . <i>Nano Letters</i> , 2010 , 10, 1271-5	11.5	6474
1	A Ferroelectric p/n Heterostructure for Highly Enhanced Short-Circuit Current Density and Self-Powered Photodetection. <i>Advanced Electronic Materials</i> , 2101385	6.4	4